
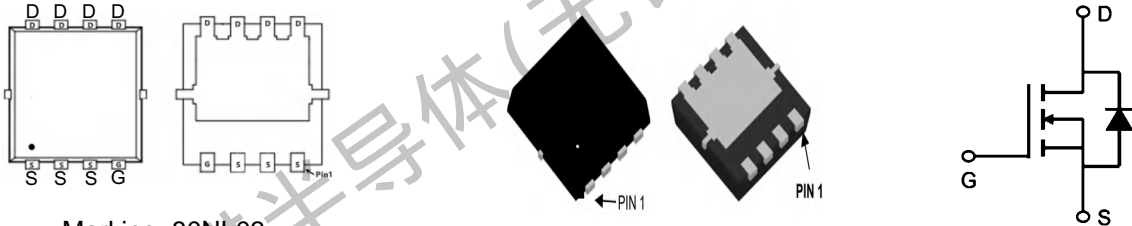


TM80NL03NF

N-Channel Enhancement Mosfet

<p>General Description</p> <ul style="list-style-type: none"> • Low R_{DS(ON)} • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>V_{DS} = 25V I_D = 80A R_{DS(ON)} = 3.5mΩ (typ.) @ V_{GS} = 4.5V</p> <p>100% UIS Tested 100% R_g Tested</p> 
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NF:DFN5x6-8L



Marking: 80NL03

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	25	V
V _{GS}	Gate-Source Voltage	±18	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 4.5V	80	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 4.5V	48	A
I _{DM}	Pulsed Drain Current	200	A
EAS	Single Pulse Avalanche Energy	58	mJ
I _{AS}	Avalanche Current	41	A
P _D @T _C =25°C	Total Power Dissipation	58	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient	---	62	°C/W
R _{θJC}	Thermal Resistance Junction-Case	---	3.6	°C/W

TM80NL03NF

N-Channel Enhancement Mosfet

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	25	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.6	0.8	1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	$V_{GS}=4.5V, I_D=30A$	-	3.5	5	m Ω
		$V_{GS}=2.5V, I_D=20A$	-	6.5	9	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V,$ $f = 1.0MHz$	-	2500	-	pF
C_{oss}	Output Capacitance		-	407	-	pF
C_{rss}	Reverse Transfer Capacitance		-	386	-	pF
Q_g	Total Gate Charge	$V_{DS}=10V, I_D=30A,$ $V_{GS}=4.5V$	-	32	-	nC
Q_{gs}	Gate-Source Charge		-	3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	11	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10V,$ $I_D=30A, R_{GEN}=3\Omega,$ $V_{GS}=4.5V$	-	17	-	ns
t_r	Turn-on Rise Time		-	49	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	74	-	ns
t_f	Turn-off Fall Time		-	26	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	80	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S=30A$	-	-	1.2	V

TM80NL03NF

N-Channel Enhancement Mosfet

Typical Performance Characteristics

Figure 1: Output Characteristics

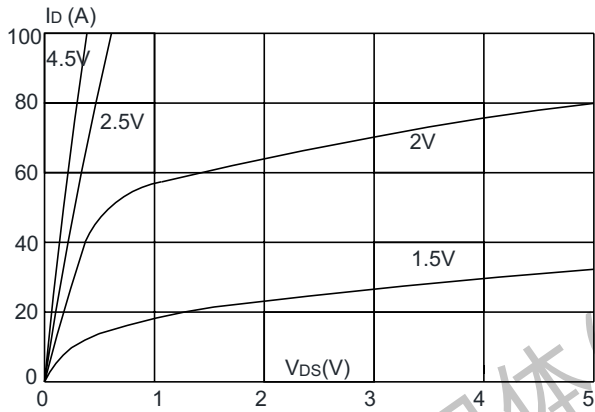


Figure 2: Typical Transfer Characteristics

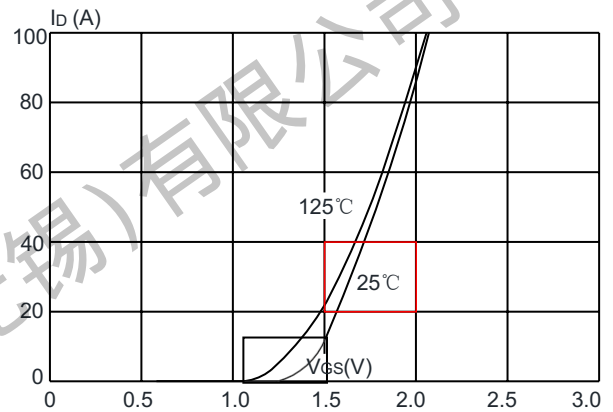


Figure 3: On-resistance vs. Drain Current

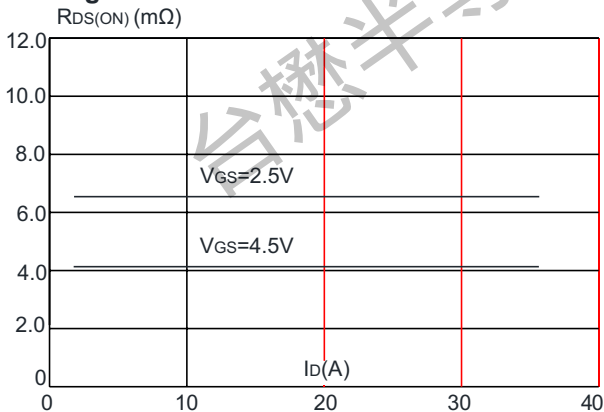


Figure 4: Body Diode Characteristics

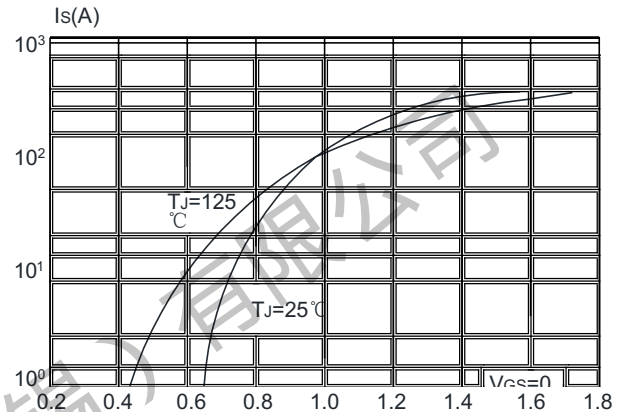


Figure 5: Gate Charge Characteristics

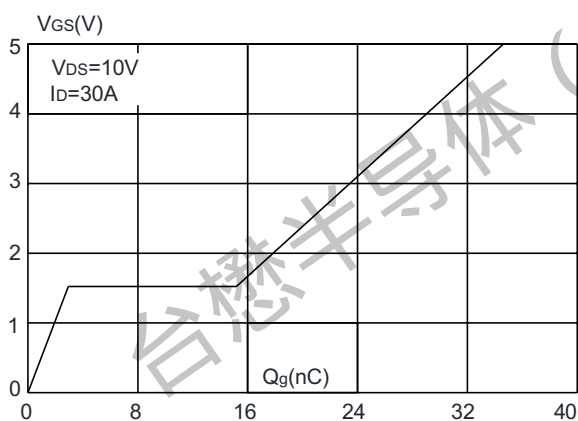
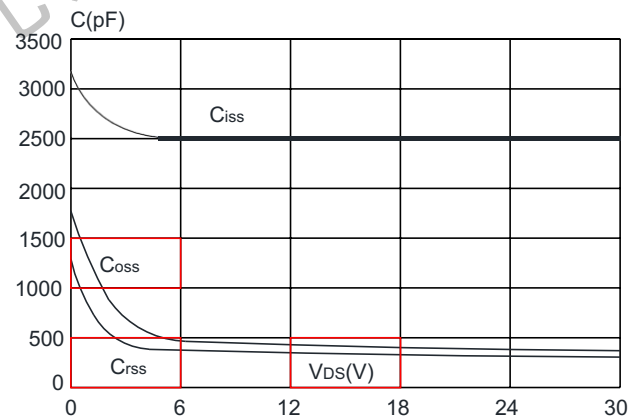


Figure 6: Capacitance Characteristics



TM80NL03NF

N-Channel Enhancement Mosfet

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

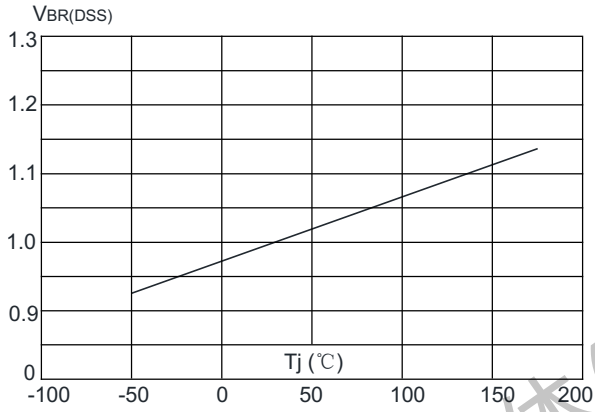


Figure 8: Normalized on Resistance vs. Junction Temperature

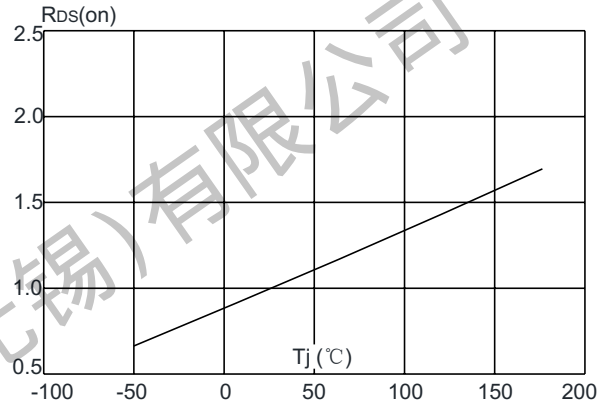


Figure 9: Maximum Safe Operating Area

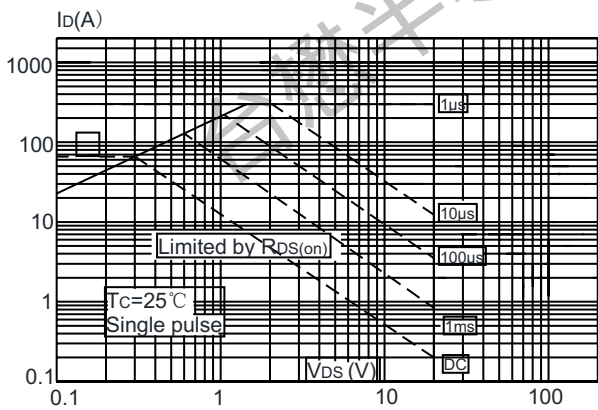


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

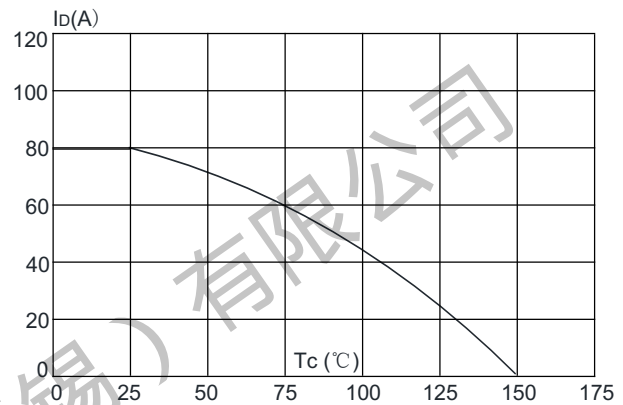
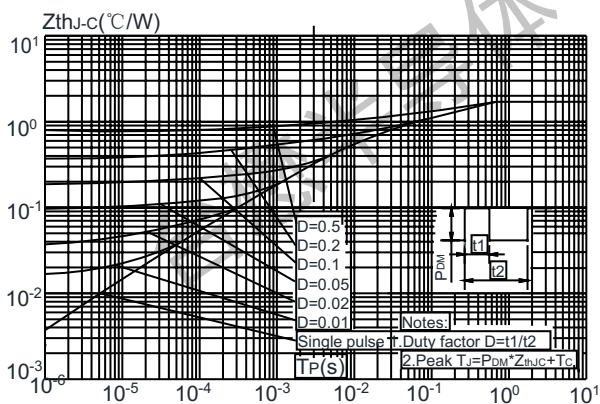


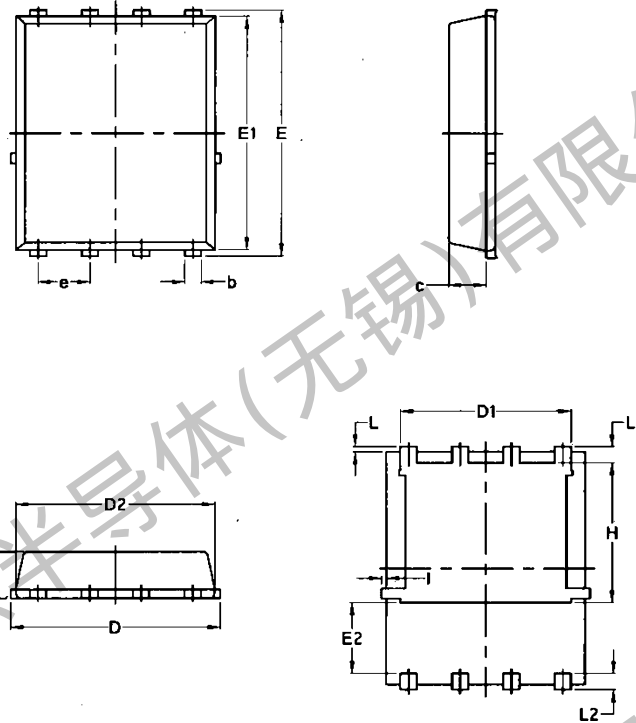
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



TM80NL03NF

N-Channel Enhancement Mosfet

Package Mechanical Data:DFN5x6-8L

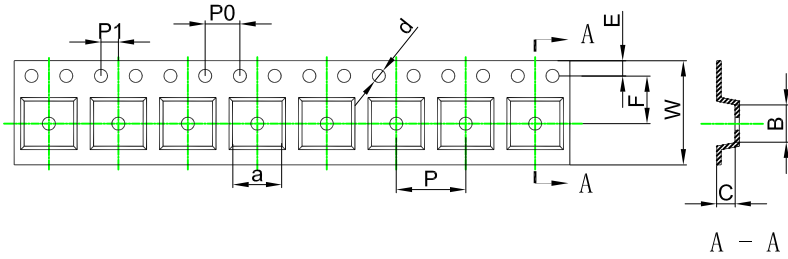


Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

TM80NL03NF

N-Channel Enhancement Mosfet

PDFN5x6-8L Embossed Carrier Tape

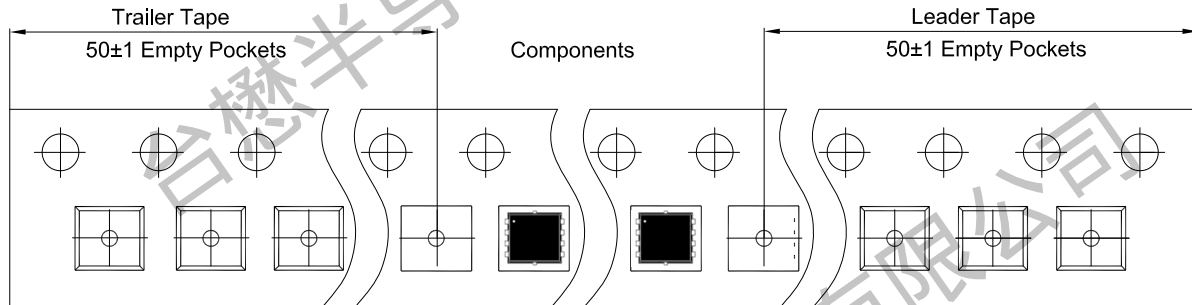


Packaging Description:

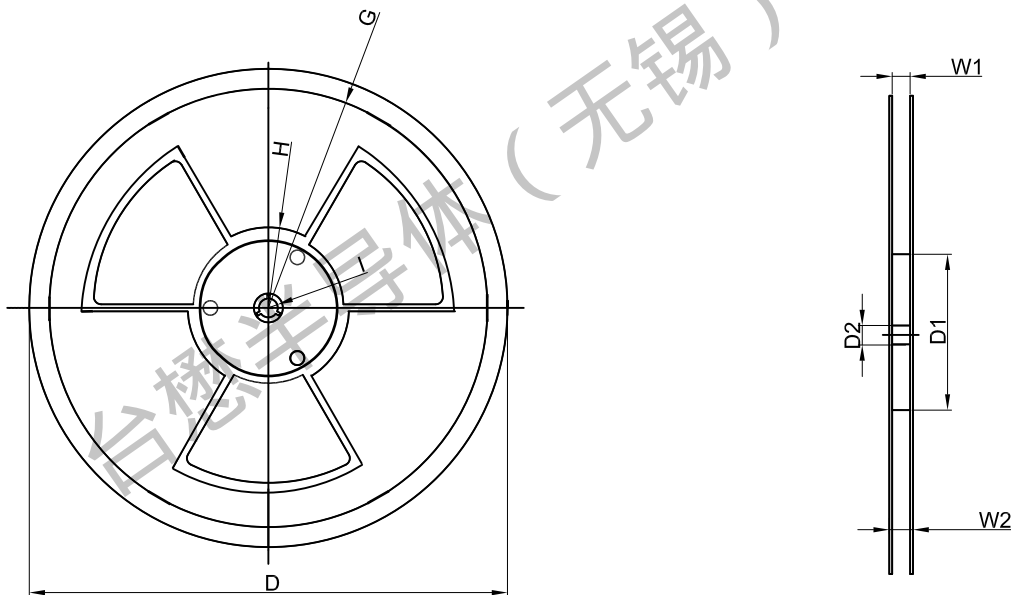
SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
PDFN5x6-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN5x6-8L Tape Leader and Trailer



PDFN5x6-8L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
5,000 pcs	13 inch	10,000 pcs	370×355×52	50,000 pcs	400×360×368	



TM80NL03NF

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Revision history:

Date	Rev	Description	Page
2023.07.18	23.07	Original	